LISTING OF THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An atomic layer depositing apparatus for forming an ultra-thin film of a semiconductor device comprising:

a reactive chamber having a ceiling;

a suscepter installed inside the reactive chamber for supporting a target substrate on which an ultra-thin film is to be formed;

at least two gas supply pipes for supplying at least two material gases into the reactive chamber to form an ultra-thin film on the substrate wherein with one of the gas supply pipes surrounding another, the gas supply pipes penetrate the ceiling of the reactive chamber to be extended to above the susceptor;

at least two gas supply controllers respectively installed at the gas supply pipes to supply the material gases alternately into the chamber;

a gas outlet for discharging the gas from the chamber;

at least two remote plasma generators installed outside the reactive chamber and respectively connected to the gas supply pipes for alternatively activating the material gases supplied through the gas supply pipes in a manner enabling operation without requiring temperature stabilization times by minimizing absorption of a reactive gas and a temperature sensitivity of a chemical reaction when materials comprising plural different components are to be deposited as the film; and

a temperature controller for controlling the temperature inside the chamber in a heat exchange method, the temperature controller being installed to surround the chamber, wherein one of the gas supply pipes surrounds another of the gas supply pipes, the gas supply pipes being arranged to penetrate the ceiling of the reactive chamber through a common inlet so as to extend to a position above the suscepter.

2. **(Currently Amended)** The atomic layer depositing apparatus of claim 1 further comprising:

a grounding unit connected both to the upper container and to the lower container of the reactive chamber to clean inside of the chamber; and

an RF power generator connected to the suscepter to apply an RF power to the suscepter.

3. **(Currently Amended)** The atomic layer depositing apparatus of claim 1, wherein a position controller for moving vertically the suscepter is additionally provided in the suscepter.

4. **(Currently Amended)** The atomic layer depositing apparatus of claim 1, wherein a vacuum pump is connected to the gas outlet.

5 - 11. (Withdrawn)